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Information Disclosure Statement for Form 1449A/PTO
INFORMATION DISCLOSURE STATEMENT BY APPLICANT
(Use as many sheets as necessary)

Complete if Known

Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Geusic, Joseph
Group Art Unit	Unknown
Examiner Name	Unknown

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Attorney Docket No: 303.390US4

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DATE CONSIDERED 08/05/2005

* EXAMINER: Initials of Examiner handwritten, either on or adjacent to the document cited. If handwritten cite is handwritten and not legible, include copy of this term with next communication to applicant. If applicant's unique citation designation number (appliance) is placed on a sheet next to the English language translation, list it here.

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Substitute for Form 1449A PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known	
		Application Number	Unknown
		Filing Date	Even Date Herewith
		First Named Inventor	Geusic, Joseph
		Group Art Unit	Unknown
		Examiner Name	Unknown
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Julie L. Halderman

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10/05/2005